



STP12NB30 STP12NB30FP

N-CHANNEL 300V - 0.34Ω - 12A TO-220/TO-220FP

PowerMESH™ MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP12NB30	300 V	< 0.40 Ω	12A
STP12NB30FP	300 V	< 0.40 Ω	12A

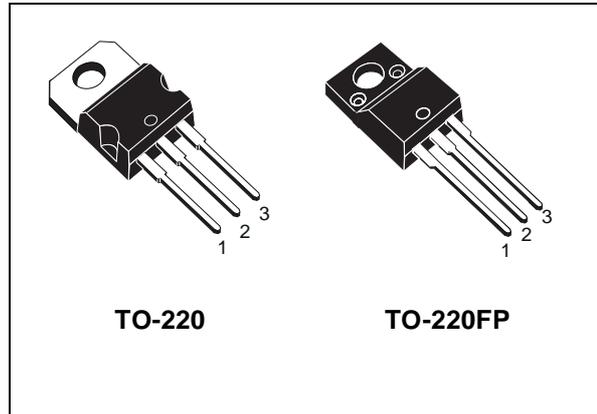
- TYPICAL R_{DS(on)} = 0.34Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performances. The new patent pending strip layout coupled with the Company's proprietary edge termination structure, gives the lowest R_{DS(on)} per area, exceptional avalanche and dv/dt capabilities and unrivalled gate charge and switching characteristics.

APPLICATIONS

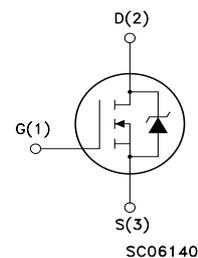
- HIGH CURRENT, HIGH SPEED SWITCHING
- UNINTERRUPTIBLE POWER SUPPLY (UPS)
- DC-DC & DC-AC CONVERTERS FOR TELECOM, INDUSTRIAL AND CONSUMER ENVIRONMENT



TO-220

TO-220FP

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP12NB30	STP12NB30FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	300		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	300		V
V _{GS}	Gate- source Voltage	± 30		V
I _D	Drain Current (continuous) at T _C = 25°C	12	12 (*)	A
I _D	Drain Current (continuous) at T _C = 100°C	7.5	7.5 (*)	A
I _{DM} (●)	Drain Current (pulsed)	48	48 (*)	A
P _{TOT}	Total Dissipation at T _C = 25°C	125	35	W
	Derating Factor	1	0.28	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	5.5		V/ns
V _{ISO}	Insulation Withstand Voltage (DC)	--	2500	V
T _{stg}	Storage Temperature	-65 to 150		°C
T _j	Max. Operating Junction Temperature			

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 60A, di/dt ≤ 400 A/μs, V_{DD} ≤ 24V, T_j ≤ T_{JMAX}
(*) Limited only by maximum temperature allowed

STP12NB30 - STP12NB30FP

THERMAL DATA

			TO-220	TO-220FP	
Rthj-case	Thermal Resistance Junction-case	Max	1	3.57	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	12	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 30 V)	250	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	300			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3	4	5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 6 A		0.34	0.4	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 6A		7.2		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		1050		pF
C _{oss}	Output Capacitance			200		pF
C _{rss}	Reverse Transfer Capacitance			25		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 150\text{ V}$, $I_D = 6\text{ A}$		18		ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		8		ns
Q_g	Total Gate Charge	$V_{DD} = 240\text{ V}$, $I_D = 12\text{ A}$,		29	40	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 10\text{ V}$		11		nC
Q_{gd}	Gate-Drain Charge			12		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Off-voltage Rise Time	$V_{clamp} = 240\text{ V}$, $I_D = 12\text{ A}$		10		ns
t_f	Fall Time	$R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$		10		ns
t_c	Cross-over Time	(see test circuit, Figure 3)		18		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				12	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				48	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 12\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,		250		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 100\text{ V}$, $T_j = 150^\circ\text{C}$		2		μC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		16		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

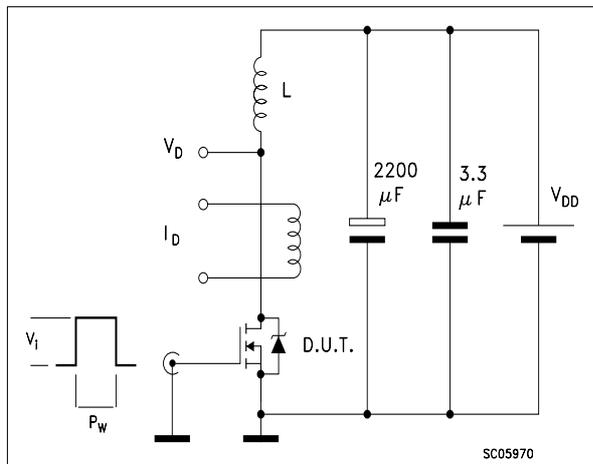


Fig. 2: Unclamped Inductive Waveform

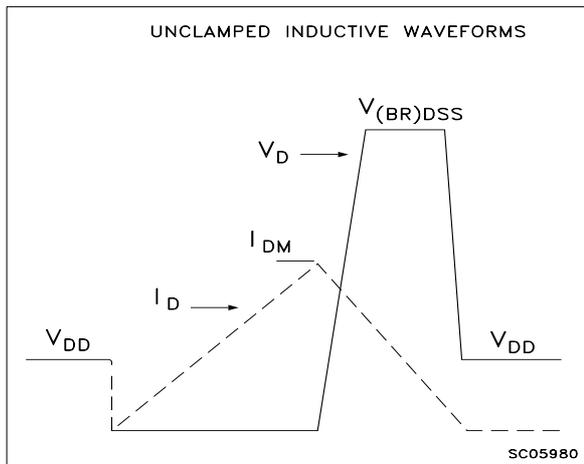


Fig. 3: Switching Times Test Circuit For Resistive Load

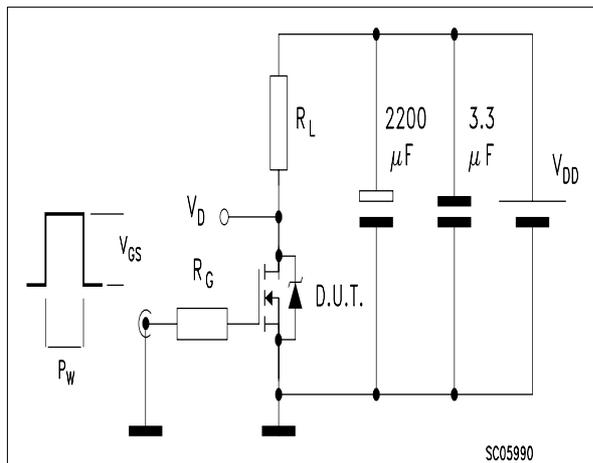


Fig. 4: Gate Charge test Circuit

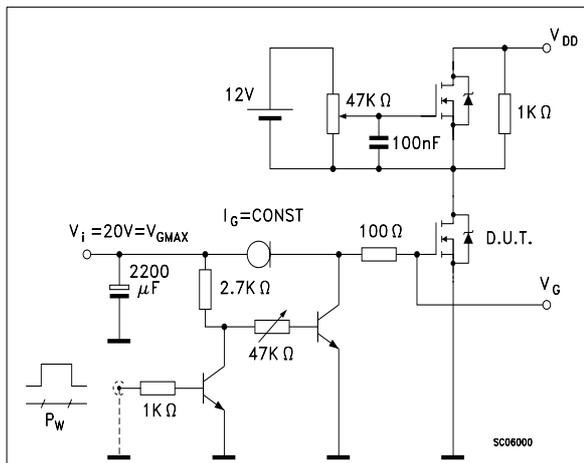
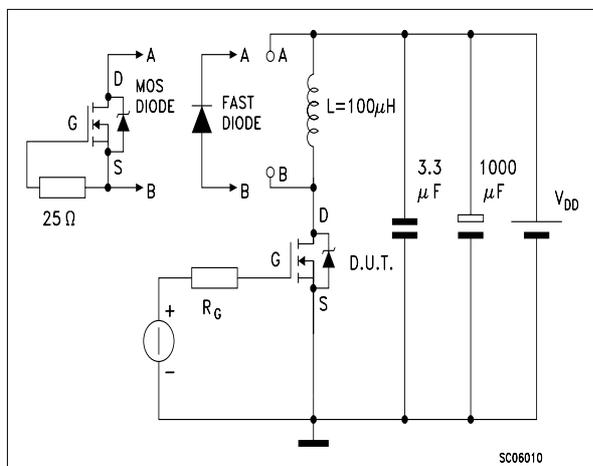
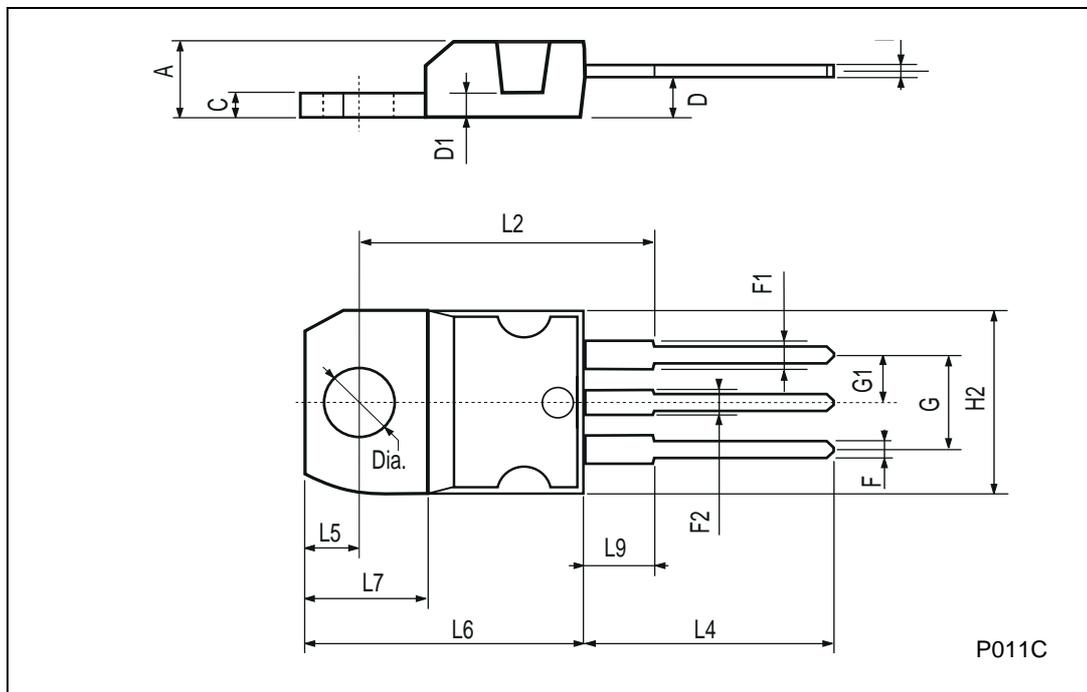


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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